

FAST RECOVERY DIODE

■ Junction Size:	Square 60 x 60 mils
■ Wafer Size:	4"
■ V_{RRM} Class:	1200 V
■ Passivation Process:	Glassivated MOAT
■ Reference IR Packaged Part:	

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1.3 V	$T_J = 25^\circ\text{C}$, $I_F = 2\text{ A}$
V_{RRM} Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 10\text{ }\mu\text{A}$ (1)
t_{rr} Typical Reverse Recovery Time	55 ns	$T_J = 25^\circ\text{C}$, $I_F = 1\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al (5 μm)
Chip Dimensions	60x60 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	260 μm , $\pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in essicated nitrogen, with no contamination

IR060PM12CS02CB

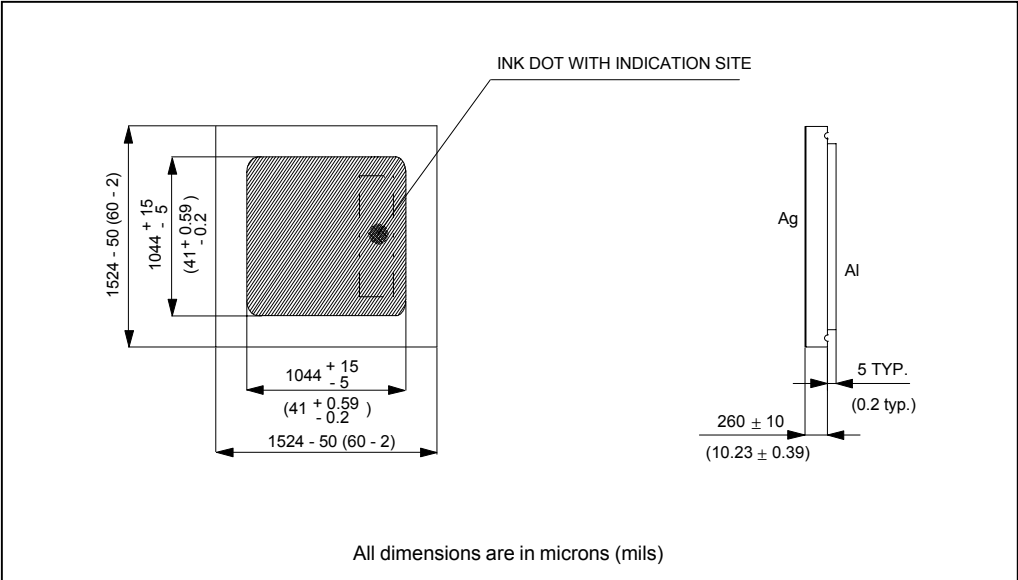
Preliminary Data Sheet I0119J rev. A 11/00

International
IR Rectifier

Ordering Information Table

Device Code							
IR	060	P	M	12	C	S02	CB
1	2	3	4	5	6	7	8
1	- International Rectifier Device						
2	- Chip Dimension in Mils						
3	- Type of Device : P = Wire Bondable Fast Recovery Diode (Platinum)						
4	- Passivation Process: M = Glassivated MOAT						
5	- Voltage code : Code x 100 = V_{RRM}						
6	- Metallization : C = Aluminium (Anode) - Silver (Cathode)						
7	- t_{rr} code						
8	- CB : Probed Uncut Die (wafer in box)						
	CF : Inked Probed Sawn wafer on film (blue tape)						

Outline Table



Wafer Layout

